

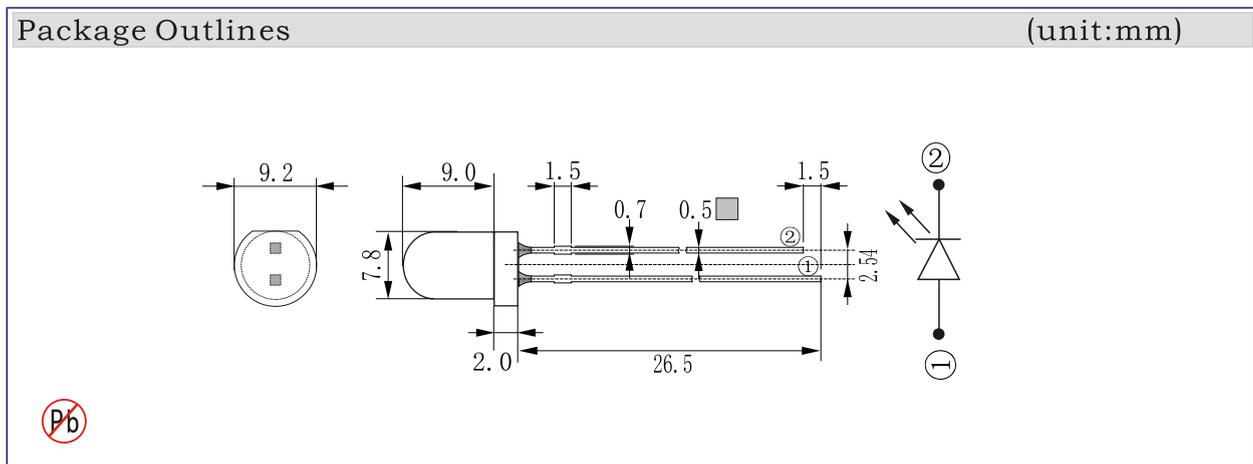
φ8mm Infrared Emitting diode

◆ABSOLUTE MAXIMUM RATING: (Ta=25°C)

Part Number	P <sub>D</sub> (mw)	V <sub>R</sub> (V)	Topr	Tstg
	100	5	-20°Cto85°C	-40°Cto85°C
PARAMETER	Power Dissipation	Reverse Voltage	Operating Temperature Range	Storage Temperature Range
Lead Soldering Temperatuer {1.6mm(0.063inch)From Body }250°C±5°CFor3Seconds				

◆ELECTRO-OPTICAL CHARACTERISTICS: (Ta=25°C)

Part Number	V <sub>F</sub> (V)			I <sub>R</sub> (μA)			λ <sub>p</sub> (nm)			2 1/2 (deg)			E <sub>e</sub> (mw/sr)		
	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX
CL-8IR3AT-P	1.2	1.6				10		850			25		7	50	
CL-8IR3AC-P	1.2	1.6				10		850			30		6	50	
TEST CONDITION	I <sub>F</sub> =20mA		V <sub>R</sub> =5V			I <sub>F</sub> =20mA			I <sub>F</sub> =20mA			I <sub>F</sub> =20mA			
	I <sub>F</sub> =100mA														



Remark : 1. All dimensions are in millimeters, tolerance is 0.25mm unless otherwise noted.  
 2. Above specification is measured by CHANGLI's test instrument and may be changed without notice.  
 3. Supplier will reserve authority on material change for above specification.